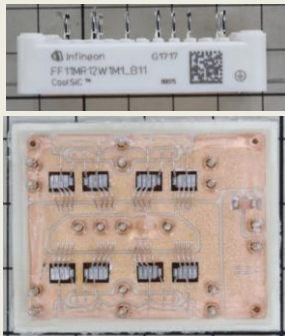


INFINEON FF11MR12W1M1_B11 CoolSiC™ HALF BRIDGE MODULE ANALYSIS REPORT

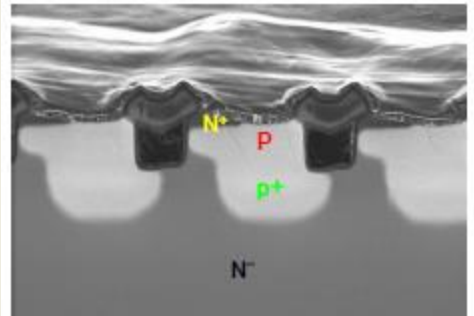
September 2017. LTEC Corporation released a detailed structure and process analysis report of this 1200V silicon carbide MOSFET power module, the 1st product using a unique asymmetric trench gate transistor design. This device has low Ron relative to comparable products from other device makers such as Rohm and Wolfspeed.



Module



SiC die



SEM cross-section

Device features

- Max. operating voltage: 1200V, rated DC Drain current $I_D=100A$ at $T_j=25^\circ C$
- Very low specific ON-resistance, $R_{ON} \times A= 360m\Omega \times mm^2$

The report has two individually purchasable sections: an 80-page Structure Analysis, and a 29-page Process Analysis section. The Structure Analysis section reveals the physical construction of the device, including EDX materials analysis, and many other fine details. The Process Analysis section includes manufacturing process flow, the estimated number of photomasking steps, and the impurity concentration of the epitaxial layer.

Note: The listed report price may not be accurate as it decreases over time.

Please contact us for current report pricing : info@ltecusa.com

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